



November 22, 2021 Sumitomo Electric Industries, Ltd Sumitomo Electric Device Innovations USA, Inc.

Gan Semiconductors are Enabling New X-band Radars

San Jose, CA – November 22, 2021 - Sumitomo Electric Industries, Ltd. and its Group company Sumitomo Electric Device Innovations USA, Inc., a leading provider of advanced radiofrequency (RF), wireless and optical communications solutions, introduce Sumitomo Electric's line of high-power gallium nitride (GaN) products for X-Band radar applications for Ground based and shipborne radars.

Next-generation X-Band radars face significant size, weight, power, and cost (SWAP-C) challenges. Among the challenges are the RF power amplifier designs used in these radar systems. Sumitomo Electric has developed a line of high-power GaN X-Band devices that enable RF solid-state power amplifiers to meet the SWAP-C challenges of these new radars while also improving reliability versus tube amplifiers. GaN provides very high power and bandwidth that improves performance, and is a proven and reliable technology for radar applications.

Sumitomo Electric remains the leader in GaN and continues to lead in innovation and technology to help customers with lower costs and improved performance for next-generation radar systems.

| | <u>SGC8595-300B-R</u> | <u>SGC0910-300B-R</u> | <u>SGC1011-300B-R</u> | <u>SGM6906VU</u> | <u>SGM6901VU</u> |
|------------|-----------------------|-----------------------|-----------------------|----------------------------|---------------------|
| Freq. | 8.5-9.5 | 9.0-10.0 | 9.8 - 10.5 | 9.2-9.5 | 8.5-10.1 |
| (GHz) | 8.3-9.3 | 9.0-10.0 | 9.8 - 10.5 | 9.2-9.5 | 8.3-10.1 |
| Power (W) | 270W <= 9.17 GHz | 270 W <= 9.6 GHz | 250 W <= 10.3 GHz | 43.7 W | 24 W<= 10.1 GHz |
| | 235 W >9.17 GHz | 235W >9.6 GHz | 220 W >10.3 GHz | | 21.4 W >10.1 GHz |
| Gain (dB) | 8.3 dB <=9.17 GHz | 8.3 dB <=9.6 GHz | 8.0 dB <=10.3 GHz | 21.4 dB | 23.3 dB |
| | 7.7 dB >9.17 GHz | 7.7 dB >9.6 GHz | 7.4 dB >10.3 GHz | | 23.3 UB |
| Efficiency | 38 % | 38 % | 37 % | 37 % | 38 % |
| Package | Hermetic | Hermetic | Hermetic | Hormotically | |
| | Metal/Ceramic | Metal/Ceramic | Metal/Ceramic | Hermetically Sealed SMT | Hermetically Sealed |
| | Flange Mount | Flange Mount | Flange Mount | | SMT |

Features of five new X-Band GaN devices:





Reference :

Sumitomo Electric Device Innovations USA, Inc.

https://www.sei-device.com